



## BULD118D-1

# HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

- INTEGRATED ANTIPARALLEL COLLECTOR- EMITTER DIODE
- HIGH VOLTAGE CAPABILITY
- LOW SPREAD OF DYNAMIC PARAMETERS
- MINIMUM LOT-TO-LOT SPREAD FOR RELIABLE OPERATION
- VERY HIGH SWITCHING SPEED

### APPLICATIONS:

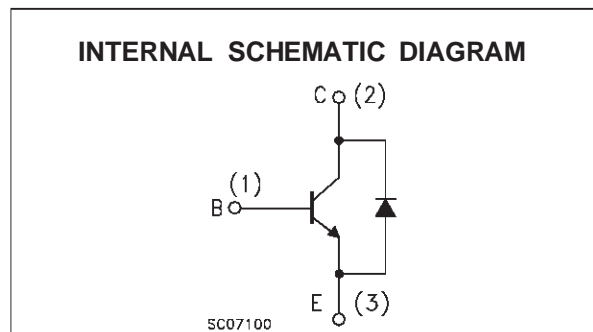
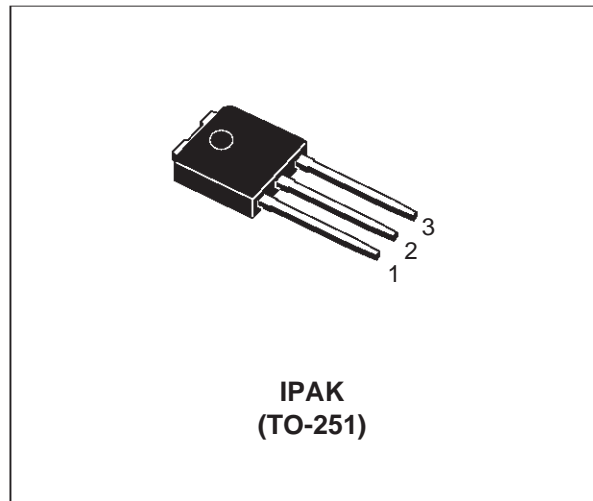
- ELECTRONIC BALLASTS FOR FLUORESCENT LIGHTING
- FLYBACK AND FORWARD SINGLE TRANSISTOR LOW POWER CONVERTERS

### DESCRIPTION

The device is manufactured using high voltage Multi Epitaxial Planar technology for high switching speeds and medium voltage capability.

It uses a Cellular Emitter structure with planar edge termination to enhance switching speeds while maintaining the wide RBSOA.

The device is designed for use in lighting applications and low cost switch-mode power supplies.



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CES}$	Collector-Emitter Voltage ( $V_{BE} = 0$ )	700	V
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )	400	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )	9	V
$I_C$	Collector Current	2	A
$I_{CM}$	Collector Peak Current ( $t_p < 5$ ms)	4	A
$I_B$	Base Current	1	A
$I_{BM}$	Base Peak Current ( $t_p < 5$ ms)	2	A
$P_{tot}$	Total Dissipation at $T_c = 25$ °C	20	W
$T_{stg}$	Storage Temperature	-65 to 150	°C
$T_j$	Max. Operating Junction Temperature	150	°C

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### THERMAL DATA

R <sub>thj-case</sub>	Thermal Resistance Junction-Case	Max	6.25	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-Ambient	Max	100	°C/W

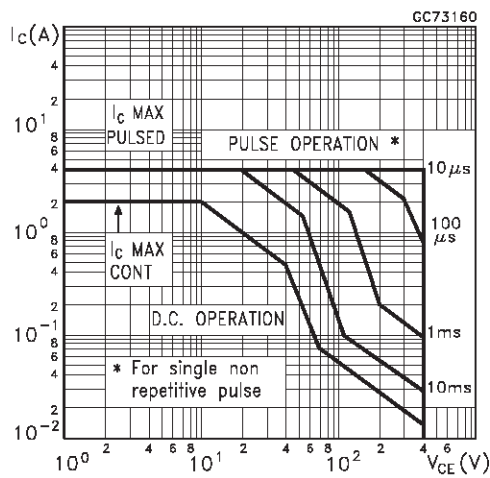
### ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I <sub>CES</sub>	Collector Cut-off Current (V <sub>BE</sub> = 0)	V <sub>CE</sub> = 700 V V <sub>CE</sub> = 700 V T <sub>j</sub> = 125 °C			100 500	μA μA
V <sub>EBO</sub>	Emitter-Base Voltage	I <sub>E</sub> = 10 mA	9			V
V <sub>CEO(sus)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 100 mA L = 25 mH	400			V
I <sub>CEO</sub>	Collector-Emitter Leakage Current	V <sub>CE</sub> = 400 V			250	μA
V <sub>CE(sat)*</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 0.5 A I <sub>C</sub> = 1 A I <sub>C</sub> = 2 A			0.5 1 1.5	V V V
V <sub>BE(sat)*</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 0.5 A I <sub>C</sub> = 1 A I <sub>C</sub> = 2 A			1.0 1.2 1.3	V V V
h <sub>FE*</sub>	DC Current Gain	I <sub>C</sub> = 10 mA I <sub>C</sub> = 0.5 A I <sub>C</sub> = 2 A				
		V <sub>CE</sub> = 5 V V <sub>CE</sub> = 5 V V <sub>CE</sub> = 5 V	10 10 8		50	
t <sub>r</sub> t <sub>f</sub> t <sub>s</sub>	RESISTIVE LOAD Rise Time Fall Time Storage Time group A group B	V <sub>CC</sub> = 125 V I <sub>B1</sub> = 0.4 A I <sub>B2</sub> = -0.2 A t <sub>p</sub> = 30 μs				
			1.4 2	0.7 0.3	0.5	μs μs μs μs
t <sub>s</sub> t <sub>f</sub>	INDUCTIVE LOAD Storage Time Fall Time	I <sub>C</sub> = 1 A V <sub>BE</sub> = -5 V V <sub>clamp</sub> = 300 V				
		I <sub>B1</sub> = 0.2 A L = 50 mH		0.8 0.10		μs μs
V <sub>F</sub>	Diode Forward Voltage	I <sub>C</sub> = 1 A			2.5	V

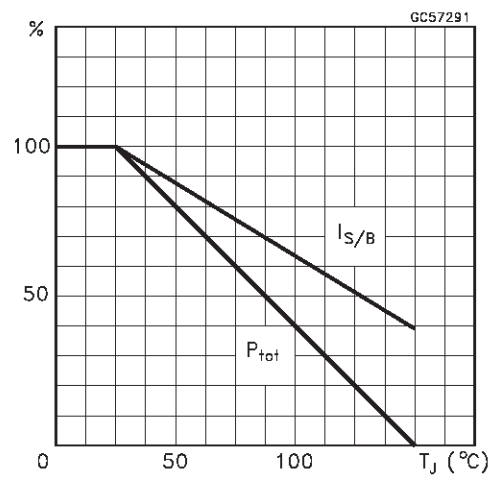
\* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

Note : Product is pre-selected in storage time (GROUP A and GROUP B). SGS-THOMSON reserves the right to ship either groups according to production availability. Please contact your nearest SGS THOMSON MICROELECTRONICS sales office for delivery details.

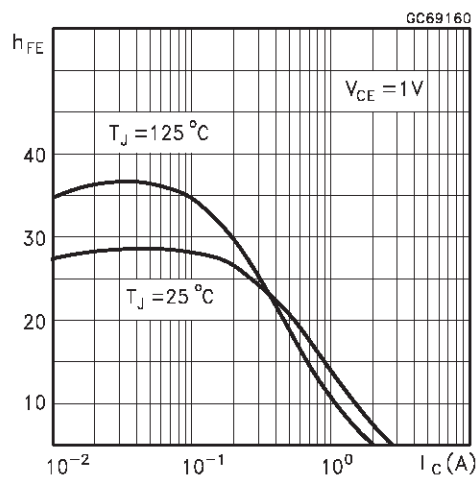
Safe Operating Areas



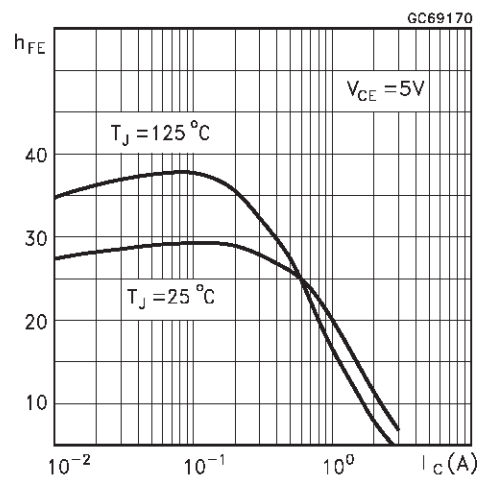
Derating Curve



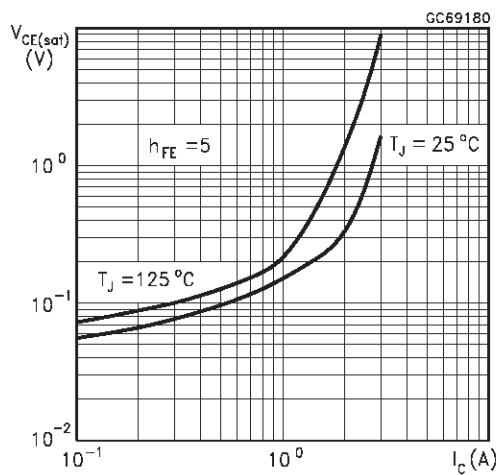
DC Current Gain



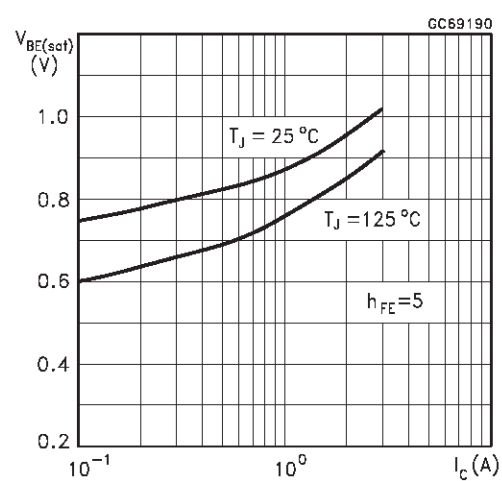
DC Current Gain



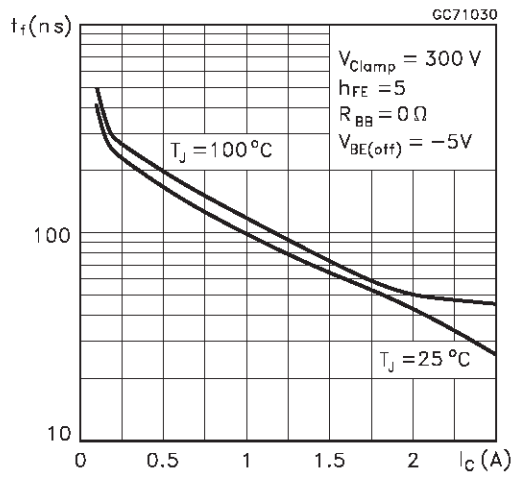
Collector Emitter Saturation Voltage



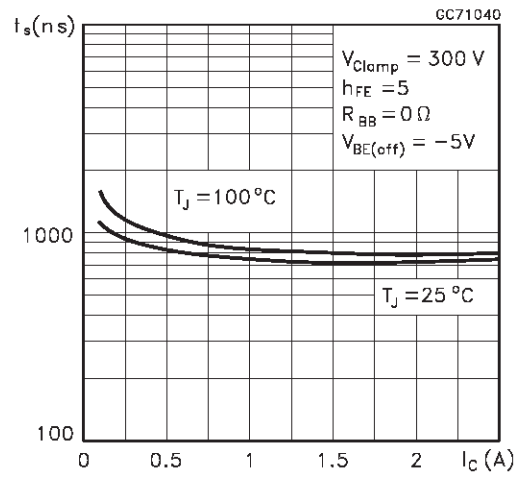
Base Emitter Saturation Voltage



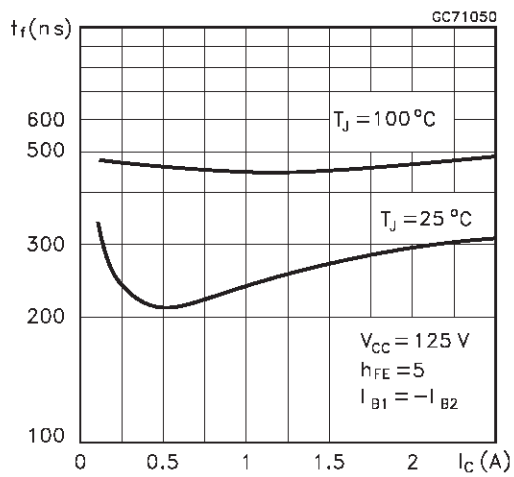
Inductive Fall Time



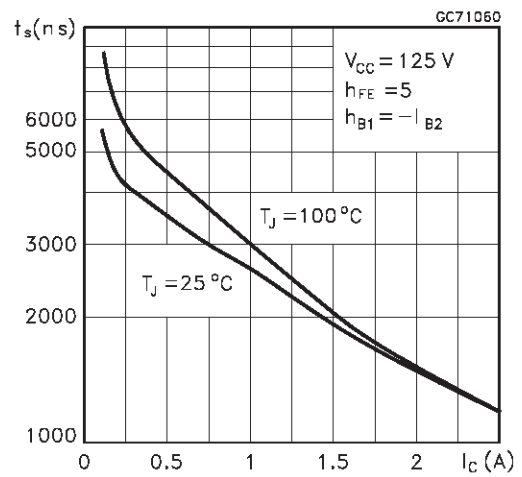
Inductive Storage Time



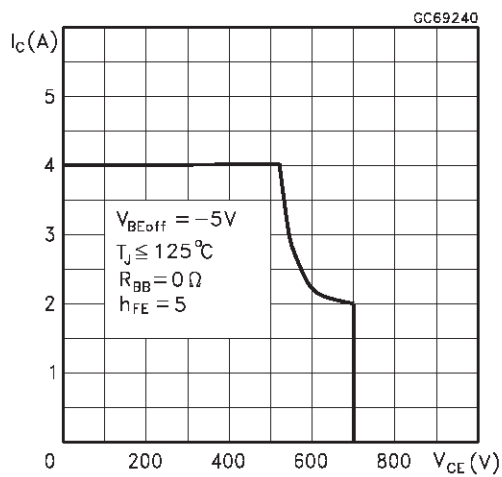
Resistive Fall Time



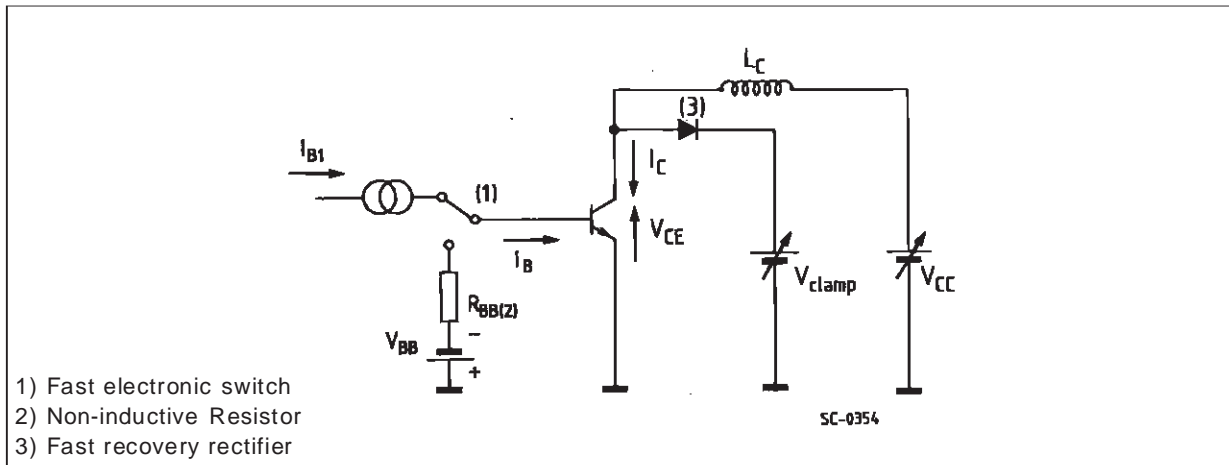
Resistive Load Storage Time



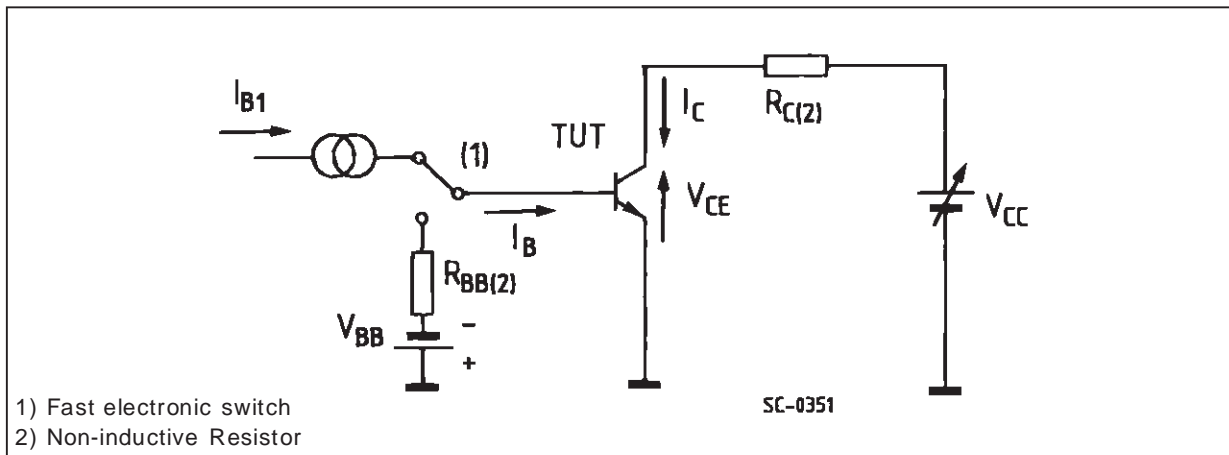
Reverse Biased SOA



**Figure 1:** Inductive Load Switching Test Circuit.

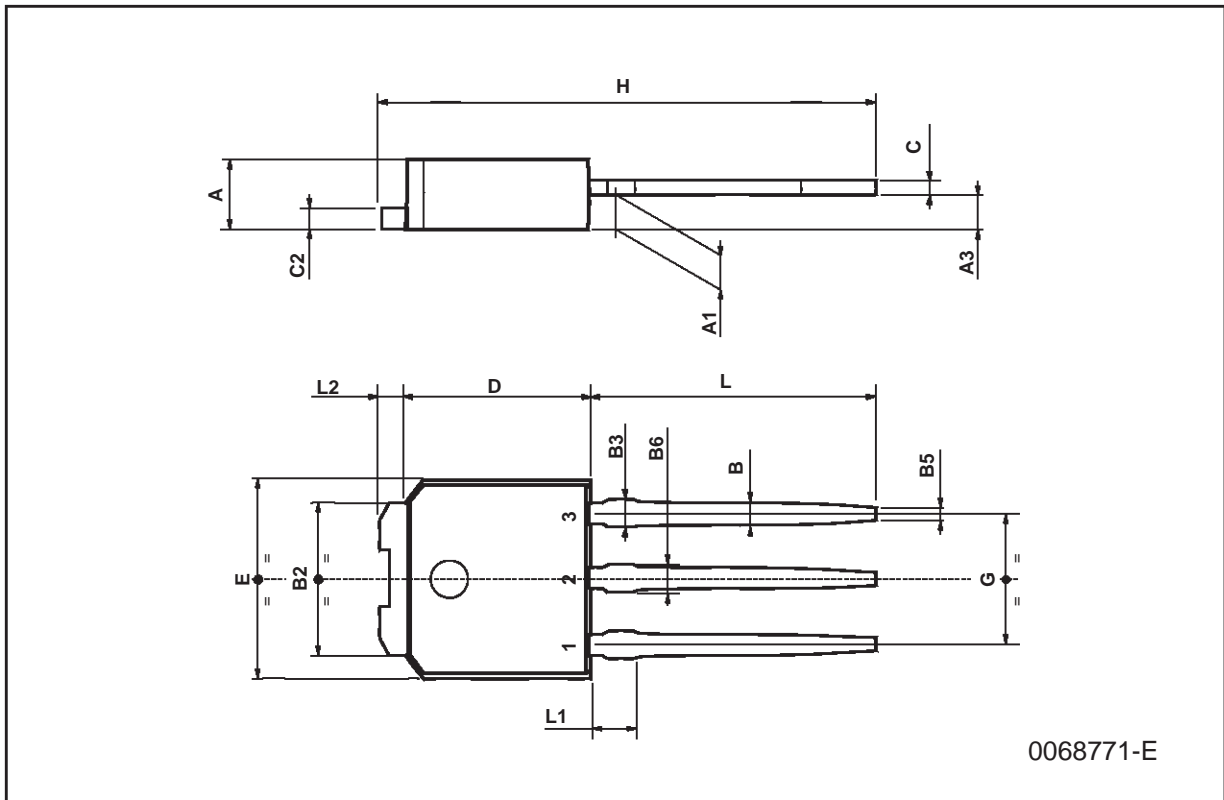


**Figure 2:** Resistive Load Switching Test Circuit.



**TO-251 (IPAK) MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
B	0.64		0.9	0.025		0.031
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.012	
B6			0.95			0.037
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039



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